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1 Introduction

Tekbox provides a complete solution for affordable pre-compliance conducted immunity testing: Coupling Decoupling Networks along with suitable calibration adapters and 150 Ohm transitions; BCI probes, suitable modulated wideband power amplifiers and EMCview PRO software. A third-party spectrum analyzer with tracking generator serves as signal source.

The TBMDA-CDN25 modulated amplifier provides the necessary power, bandwidth and modulation for conducted immunity testing using CDNs and with certain limitations BCI probes in the frequency range from 100 kHz to 250 MHz. It is designed to be driven by signal generators or by tracking generators of spectrum analyzers. With a 1 dB compression point of up to 25 W in the frequency range 100 kHz to 250 MHz it can generate test levels class 1, class 2, class 3 with CDNs according to ISO / EN 61000-4-6. A built in AM / PM - modulator enables use of tracking generators as signal source. The TBMDA-CDN25 has sufficient gain to achieve maximum output power with 0 dBm provided by a spectrum analyzer tracking generator. Besides 1 kHz, 80% AM, the TBMDA-CDN25 provides built in modulation capability to generate 1 kHz, 50% duty cycle PM signals. In PM mode, the TBMDA-CDN25 can also generate a 217 Hz Signal with 12.5% duty cycle in order to simulate mobile phone TDMA noise.



Picture 1 - TBMDA-CDN25 modulated wideband driver amplifier, front view



Picture 2 - TBMDA-CDN25 modulated wideband driver amplifier, rear view

V1.1 TBMDA-CDN25



Modulated Wideband Power Amplifier

Application:

General-purpose wideband RF power amplifier Wideband RF power amplifier for conducted immunity testing driving CDNs or BCI-probes Wideband RF power amplifier for radiated immunity testing, driving near field probes Wideband RF power amplifier for radiated immunity testing, driving TEM Cells <u>Features:</u> CW amplifier (modulation off)

1 kHz, 80% AM modulation
1 kHz, 50% duty cycle pulse modulation
217 Hz, 12.5% duty cycle pulse modulation

Dimensions:

32 cm x 28 cm x 13 cm, 5.7 kg

2 Electrical Specifications

Technical Data:

Input / Output: 50 Ohm, N female Supply Voltage range: 110 V...240 V Supply power consumption: 108 W @ 220V Operating temperature range: -20°C to 50°C Frequency range: 100 kHz - 250 MHz Small signal gain: 47 dB typ. Gain flatness 100 kHz – 250 MHz / Pin = -3 dBm: 3.5 dB typ. Saturated output power @ 100 kHz / Pin = 0 dBm: 44.1 dBm (25.7 W) typ. Saturated output power @ 150 kHz / Pin = 0 dBm: 44.6 dBm (28.8 W) typ. Saturated output power @ 500 kHz / Pin = 0 dBm: 45.1 dBm (32.4 W) typ. Saturated output power @ 1 MHz / Pin = 0 dBm: 45.3 dBm (33.9 W) typ. Saturated output power @ 10 MHz / Pin = 0 dBm: 45.3 dBm (33.9 W) typ. Saturated output power @ 50 MHz / Pin = 0 dBm: 45.6 dBm (36.3 W) typ. Saturated output power @ 80 MHz / Pin = 0 dBm: 46.6 dBm (45.7 W) typ. Saturated output power @ 100 MHz / Pin = 0 dBm: 46.5 dBm (44.7 W) typ. Saturated output power @ 150 MHz / Pin = 0 dBm: 44.5 dBm (28.2 W) typ. Saturated output power @ 200 MHz / Pin = 0 dBm: 43.8 dBm (24 W) typ. Saturated output power @ 230 MHz / Pin = 0 dBm: 44.9 dBm (30.9 W) typ. Saturated output power @ 250 MHz / Pin = 0 dBm: 44.8 dBm (30.2 W) typ.





1dB output compression point @ 100 kHz: +43.7 dBm typ. (Pin: -5 dBm)	
1dB output compression point @ 150 kHz: +44.1 dBm typ. (Pin: -4 dBm)	
1dB output compression point @ 500 kHz: +44.6 dBm typ. (Pin: -3 dBm)	
1dB output compression point @ 1 MHz: +45 dBm typ. (Pin: -3 dBm)	
1dB output compression point @ 10 MHz: +45 dBm typ. (Pin: -2 dBm)	
1dB output compression point @ 50 MHz: +45.6 dBm typ. (Pin: 1 dBm)	
1dB output compression point @ 80 MHz: +46.5 dBm typ. (Pin: 1 dBm)	
1dB output compression point @ 100 MHz: +46.5 dBm typ. (Pin: 0 dBm)	
1dB output compression point @ 150 MHz: +42.9 dBm typ. (Pin: -4 dBm)	
1dB output compression point @ 200 MHz: +42.2 dBm typ. (Pin: -4 dBm)	
1dB output compression point @ 230 MHz: +44.1 dBm typ. (Pin: -3 dBm)	
1dB output compression point @ 250 MHz: +43 dBm typ. (Pin: -4 dBm)	
2 nd harmonic, 100 MHz, Pout=46dBm: < - 12 dBc typ.	
2 nd harmonic, 100 MHz, Pout=40dBm: < - 15 dBc typ.	
3 rd harmonic, 100 MHz, Pout=46dBm: < - 22 dBc typ.	
3 rd harmonic, 100 MHz, Pout=40dBm: < - 22 dBc typ.	
Total harmonic distortion:	
17.7% @100MHz, Pout=37dBm typ.	
19.6% @100 MHz, Pout=40 dBm typ.	
22.1% @100 MHz, Pout=43 dBm typ.	
26.9% @100 MHz, Pout=46 dBm typ.	
Third order output intercept point: +51 dBm, @100 MHz, Δ f = 2MHz, typ.	
Internal modulation frequency AM: 1 kHz ±20%	
Internal modulation frequencies PM: 1 kHz ±20%, 217 Hz ±20%	
Duty cycle, PM: 50% ±10% @ 1 kHz; 12.5% ±20% @ 217 Hz	

Maximum ratings:

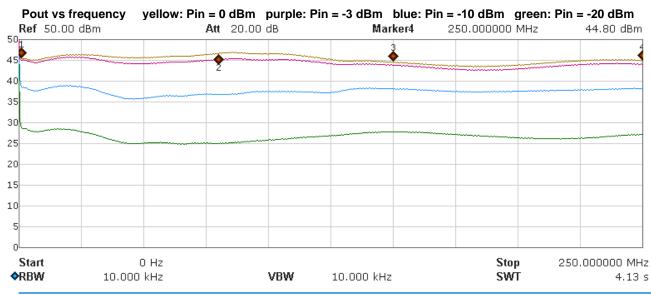
Maximum input power: +3 dBm

The output of the TBMDA-CDN25 is quite tolerant to output mismatch, however open or shorted load is not recommended, as it potentially can cause damage to the output transistor. When driving near field probes, current probes or any load of unknown impedance, it is highly recommended to insert $a \ge 3dB$ attenuator at the output of the amplifier in order to protect the output stage.





Gain flatness:



Marker Table

Marker	Тгасе	Readout	X Axis	Ampt
Marker1	А	Frequency	1.000000 MHz	45.29 dBm
Marker2	А	Frequency	80.000000 MHz	46.56 dBm
Marker3	A	Frequency	150.000000 MHz	44.45 dBm
Marker4	A	Frequency	250.000000 MHz	44.80 dBm

Small Signal Performance (@ Pin = - 10 dBm):

Frequency [MHz]	0.1	0.15	0.5	1	10	50	80	100	150	200	230	250
Output power [dBm]	39.44	39.19	38.66	38.46	38.00	35.79	36.75	37.44	38.05	37.49	37.84	38.07
Gain [dB]	49.44	49.19	48.66	48.46	48.00	45.79	46.75	47.44	48.05	47.49	47.84	48.07

Table 1 – TBMDA-CDN25 small signal gain, typ.

1 dB compression point:

Frequency [MHz]	0.1	0.15	0.5	1	10	50	80	100	150	200	230	250
Output power [dBm]	43.36	44.06	44.57	44.98	45.04	45.62	46.54	46.46	42.86	42.23	44.01	43.02
Pin [dBm]	-5	-4	-3	-3	-2	1	1	0	-4	-4	-3	-4

Table 2 – TBMDA-CDN25, 1 dB compression point versus frequency, typ.

Saturation (@ Pin = 0 dBm):

Output power [dBm] 44.12 44.62 45.07 45.29 45.34 45.56 46.56 46.46 44.45 43.76 44.93 44.80 Gain [dB] 44.12 44.62 45.07 45.29 45.34 45.56 46.56 46.46 44.45 43.76 44.93 44.80	Frequency [MHz]	0.1	0.15	0.5	1	10	50	80	100	150	200	230	250
Gain [dB] 44.12 44.62 45.07 45.29 45.34 45.56 46.56 46.46 44.45 43.76 44.93 44.80	Output power [dBm]	44.12	44.62	45.07	45.29	45.34	45.56	46.56	46.46	44.45	43.76	44.93	44.80
	Gain [dB]	44.12	44.62	45.07	45.29	45.34	45.56	46.56	46.46	44.45	43.76	44.93	44.80

Table 3 – TBMDA-CDN25, Saturation versus frequency, typ.





Modulation:

Zero span, 10 ms sweep time, peak detector

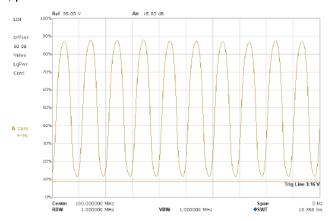


Figure 1 – 1 kHz, 80 % AM, envelope, 100 MHz, Pout = 44 dBm peak;

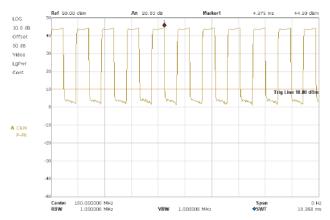


Figure 2 – 1 kHz, 50 % PM envelope, 100 MHz, Pout = 44 dBm peak

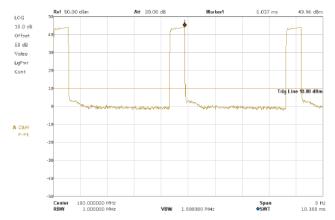


Figure 3 – 217 Hz, 12.5 % PM envelope, 100 MHz, Pout = 44 dBm peak





3 Applications - radiated immunity

Immunity testing using a TEM cell

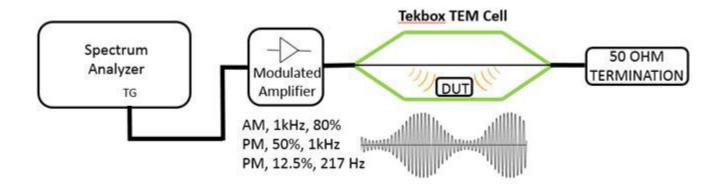


Figure 4 – immunity testing set up

Immunity testing using near field probes

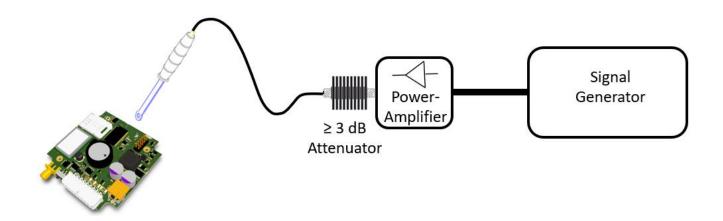


Figure 5 - immunity testing set up to locate susceptible areas on PCBAs

Radiated immunity EMC pre-compliance is typically a 2-step procedure. First, a TEM cell is used to investigate for immunity issues of the DUT. In case of any failure, near-field probes will be used to locate the sensitive circuitry on the PCBA.





TEM Cell field strength

A typical pre-compliance set up for immunity testing is typically not equipped with an E-field probe to measure the real field strength inside the TEM cell. However, the field strength can be calculated with sufficient accuracy for EMC pre-compliance set-ups.

The E-field (V/m) between septum and lower (upper) wall of a TEM cell is E = V/d where V is the RMS voltage of the applied signal and d is the distance between septum and lower (upper) wall. This is based on the simplified assumption that the E field would be perfectly homogenous/evenly distributed. A more practical formula is $E = V^*$ Cor/d where Cor is a correction factor for the average field strength over the volume of the DUT derived from the analysis of the field distribution over the cross section of the cell.

Assuming the DUT is placed in the center of the cell and in the middle between bottom wall and septum, we can use the simplified formula with sufficient accuracy.

TBTC0: d = 2.8 cm -> $E_{V/m} = (\sqrt{P^*50\Omega})^*35.7$ TBTC1: d = 5 cm -> $E_{V/m} = (\sqrt{P^*50\Omega})^*20$ TBTC2: d = 10 cm -> $E_{V/m} = (\sqrt{P^*50\Omega})^*10$ TBTC3: d = 15 cm -> $E_{V/m} = (\sqrt{P^*50\Omega})^*6.66$

The power P in the formulas above hast to be entered in [Watt] P $_{[W]} = 0.001^{*}(10^{\Lambda} (P_{[dBm]}/10))$

Frequency [MHz]	Input power [dBm]	Output power [dBm]	Field strength TBTC0 [V/m]	Field strength TBTC1 [V/m]	Field strength TBTC2 [V/m]	Field strength TBTC3 [V/m]
0.1	-3	43.86	1245	697	349	232
0.15	-3	44.32	1313	735	368	245
0.5	-3	44.57	1351	757	378	252
1	-3	44.98	1416	793	397	264
10	-3	44.76	1381	774	387	258
50	-3	44.13	1284	719	360	240
80	-3	45.07	1431	802	401	267
100	-3	45.01	1421	796	398	265
150	-3	43.77	1232	690	345	230
200	-3	42.86	1110	622	311	207
230	-3	44.01	1267	710	355	236
250	-3	43.92	1254	702	351	234

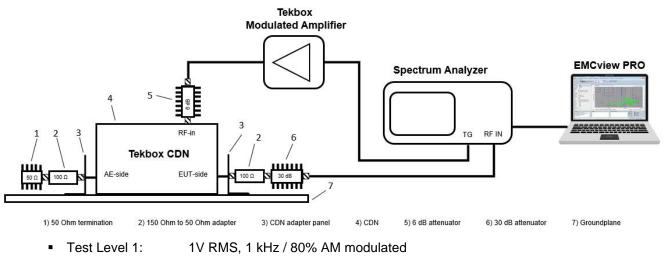
Table 4 – calculated field strength for the TBMDA-CDN25 driving Tekbox TEM cells

The above output power is the RMS output power in case of a CW signal. Note that in case of 80% AM modulation, the RMS power of the modulated signal will be 5.1 dB lower than the RMS power of the CW signal.



4 Applications - conducted immunity, using CDNs

EN 61000-4-6 calibration set up using EMCview PRO



- Test Level 2: 3V RMS, 1 kHz / 80% AM modulated
- Test Level 3: 10V RMS, 1 kHz / 80% AM modulated
- Test Level X: special (unspecified)

The specified test levels are open circuit voltages at the EUT port of the CDN.

The voltages measured during calibration must be multiplied by 3 to allow for the 50 Ohm to 150 Ohm conversion and again by 2 to reach the open circuit voltage.

Hence, the measured voltage at the output of the 150 Ohm to 50 Ohm adapter is 1/6 th the voltage of the desired stress level. In logarithmic figures, the measured voltage is 15.5 dB lower than the open circuit voltage.

Example: Test level 2

 U_0 = 3V RMS open circuit voltage at the EUT port of the CDN = 3V/6 = 0.5V RMS at the output of the 100 Ohm to 50 Ohm adapter.

The required power at the output of the modulated amplifier is:

U₀/6 [dBm] + CDN insertion loss + 6 dB (Attenuator) + 5.1 dB (80% AM RMS)

Assuming 10 dB insertion loss for the CDN, the required RF power is:

7 dBm + 10 dB + 6 dB + 5.1 dB = 28.1 dBm = 0.65 Watt

During calibration, EMCview Pro will make a stepped sweep, for each frequency adjusting the tracking generator level in order to achieve 7 dBm + 5.1 dB -30 dB = -17.9 dBm at the spectrum analyzer input. The tracking generator level table will then be used to set levels during the actual immunity test.

Note that the above calculation does not include tolerances of the cable, attenuator and CDN.

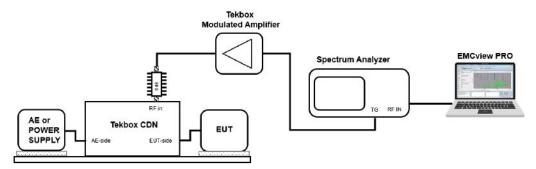




Test levels that can be achieved with the TBMD-CDN25:

Amplifier model	Modulation	Attenuator	Test levels	Freq. Range
TBMDA-CDN25	AM 80%, 1 kHz	6 dB	Level 1, Level 2, Level 3	150 kHz – 230 MHz

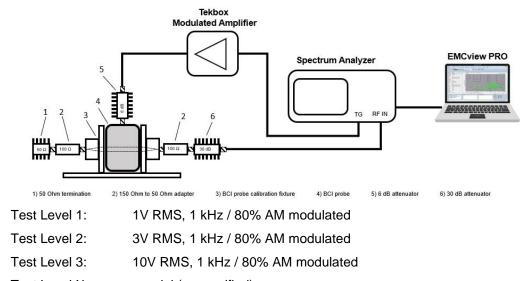
EN 61000-4-6 immunity test set up using EMCview PRO



Set up the CDN and DUT as shown above. In EMCview PRO, load the file created during calibration and press the Play-button to run the immunity test.

5 Applications - conducted immunity, using BCI probes

EN 61000-4-6 300 Ohm loop BCI calibration set up using EMCview PRO



Test Level X: special (unspecified)

The specified test levels are open circuit voltages at the output of the calibration fixture.



The voltages measured during calibration must be multiplied by 3 to allow for the 50 Ohm to 150 Ohm conversion and again by 2 to reach the open circuit voltage.

Hence, the measured voltage at the output of the 150 Ohm to 50 Ohm adapter is 1/6th the voltage of the desired stress level. In logarithmic figures, the measured voltage is 15.5 dB lower than the open circuit voltage.

<u>Example</u>: Test level 1 U₀= 1V RMS open circuit voltage at the output of the calibration fixture = 1V/6 = 0.166V RMS at the output of the 100 Ohm to 50 Ohm adapter.

The required power at the output of the modulated amplifier is:

U₀/6 [dBm] + BCI probe insertion loss + 6 dB (Attenuator) + 5.1 dB (80% AM RMS)

Assuming 16 dB insertion loss for the BCI probe in a 300 Ohm loop, the required RF power is:

-2.55 dBm + 16 dB + 6 dB + 5.1 dB = 24.55 dBm = 0.28 Watt

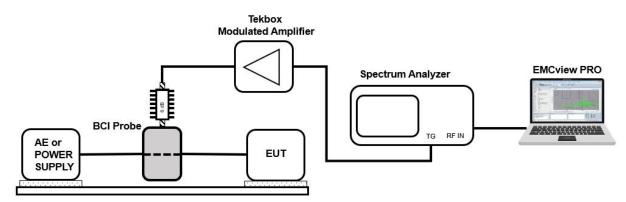
During calibration, EMCview Pro will make a stepped sweep, for each frequency adjusting the tracking generator level in order to achieve -2.55 dBm + 5.1 dB -30 dB = -27.55 dBm at the spectrum analyzer input. The tracking generator level table will then be used to set levels during the actual immunity test.

Note that the calculation does not include any tolerances of the BCI probe, attenuator and cable. The BCI probe within the 300 Ohm loop has a higher coupling loss compared to the probe within a 50 Ohm system. It will exceed the 16 dB used for the above example at frequencies below 500kHz.

The BCI method requires significantly more power than the CDN method, to achieve the same stress levels. Test levels that can be achieved with the TBMDA-CDN25:

Amplifier model	Modulation	Attenuator	Test levels	Freq. Range
TBMDA5	AM 80%, 1 kHz	6 dB	Level 1, Level 2, 5V	150 kHz – 230 MHz
	AM 80%, 1 kHz	3 dB	Level 1, Level 2, 8V	150 kHz – 230 MHz

EN 61000-4-6 immunity test set up using a BCI probe and EMCview PRO



Set up the test equipment and DUT as shown above. In EMCview PRO, load the file created during calibration and press the Play-button to run the immunity test.



ISO 11452-4 substitution method using EMCview PRO

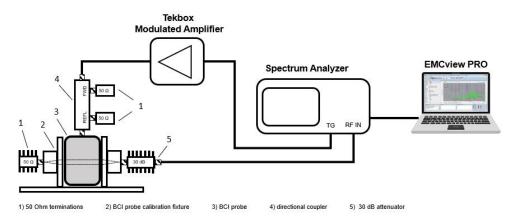
The automotive immunity standard ISO 11452-4 as well as immunity standards for defense and avionic products specify stress levels in terms of induced disturbance current.

Traditional calibration and test methods use current monitoring probes in order to create a control loop, thereby maintaining the required disturbance current. Levelling loops can be fooled by cable resonances. High impedance resonances cause the RF amplifiers output power to raise, in order to achieve the specified disturbance current. Similarly, low impedance resonances may significantly reduce the RF amplifiers output power. This situation is unrealistic of most real-life electromagnetic environments and could create a severe over-test or under-test situation.

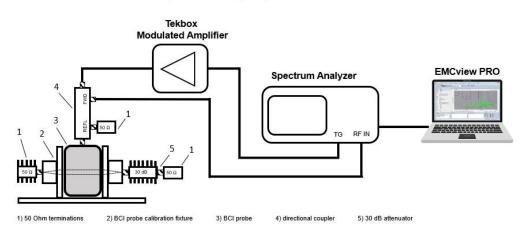
In order to get around the over-test / under-test problems associated with the closed loop test method, the standards offer the substitution method (open loop), where the disturbance current is set by measuring current induced into a 100 Ohm loop. Forward and reflected power is measured using a directional coupler while setting the RF power to achieve the required disturbance current levels into the 50 Ohm load. During actual immunity test, the forward power level is set according to the value recorded during calibration.

Substitution calibration method set up for pre-compliance purpose:

Substitution method, calibration, step 1



Substitution method, calibration, step 2



V1.1 TBMDA-CDN25



Modulated Wideband Power Amplifier

Example: Test level I – 60 mA A power of 22.6 dBm is required to achieve a current of 60 mA in a 50 Ohm load. Assume 8dB insertion loss for a typical BCI probe in a 100 Ohm loop. Assume 1 dB insertion loss for the directional coupler The required power at the output of the modulated amplifier is: Test level [dBm] + BCI probe insertion loss + 6 dB (Attenuator) + 5.1 dB (80% AM RMS) 22.6 dBm + 8 dB + 1 dB + 5.1 dB = 36,7 dBm = 4.7 W

Example: Test level IV - 200 mA

A power of 33 dBm is required to achieve a current of 200 mA in a 50 Ohm load.

Assume 8dB insertion loss for a typical BCI probe in a 100 Ohm loop.

Assume 1 dB insertion loss for the directional coupler

The required power at the output of the modulated amplifier is:

Test level [dBm] + BCI probe insertion loss + 6 dB (Attenuator) + 5.1 dB (80% AM RMS)

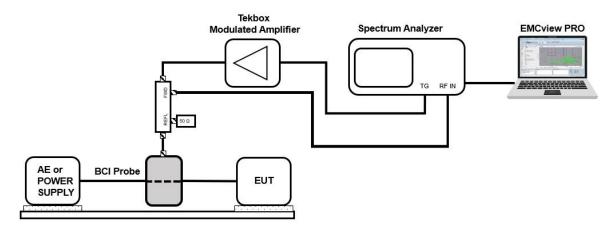
33 dBm + 8 dB + 1 dB + 5.1 dB = 47.1 dBm = 51.3 W

Note that the TBMDA-CDN25 is not suitable for immunity testing according to ISO 11452-4, as it cannot cover the entire frequency range up to 400 MHz.

Test levels and frequency range that can be achieved with the TBMDA-CDN25

Amplifier model	Modulation	Test levels	Freq. Range	
TBMDA-CDN25	AM 80%, 1 kHz	Level I, Level II	1 MHz - 230 MHz	
	CW	Level I - Level IV	1 MHz - 230 MHz	

Substitution method, immunity test



Set up the test equipment and DUT as shown above. In EMCview PRO, load the file created during calibration and press the Play-button to run the immunity test.



ISO 11452-4 closed loop method using EMCview PRO

The Closed Loop Method controls the injected current by measuring the actual injected current using a current probe.

The injected current depends on the impedance of the EUT and cable and may not be achievable for any frequency, especially if ungrounded EUTs are used. At parallel resonances of the cable, the impedance will become very high and maintaining the set current level might exceed the capabilities of the RF power amplifier. This is a common issue associated with the closed loop method.

The currently available modulated amplifiers from Tekbox do not provide sufficient power, except perhaps for Level I. Typically, amplifiers with 100 – 250W output power are used for closed loop immunity tests.

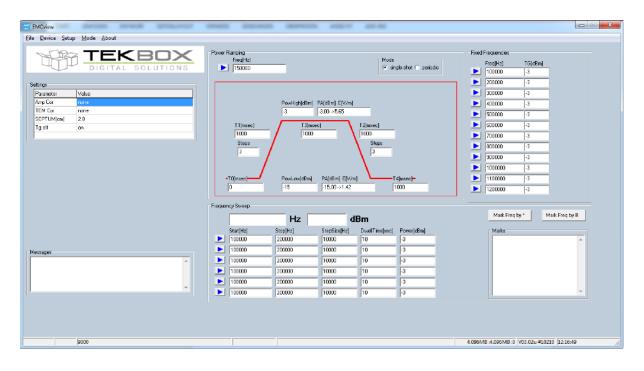
6 PC Software for immunity testing

Tekbox provides two software versions for EMC pre-compliance measurements

EMCview provides a feature to control the tracking generator output frequency and level and carry out sweeps with constant tracking generator level.

EMCview PRO provides a more sophisticated feature, which is able to carry out calibration sweeps for CDN and BCI based set ups. The resulting calibration file is used to set the tracking generator level during the immunity test sweep.

Tekbox EMCview currently supports Rigol, Siglent, Owon, R&S FPC and FPH series spectrum analyzers. Refer to the EMCview website for the latest list of supported models



screenshot of the tracking generator control feature of EMCview / EMCview Pro





Immunity Test Setup Cali	bration	Immunity Measurement EN 61	000-4-6 CDN
Parameter	Value	Parameter	Value
Freq Start[Hz]	150000	Calibration	none
Freq Stop[Hz]	8000000	Freg Start Sweep[Hz]	150000
Freq Step[%]	10	Freq Stop Sweep[Hz]	80000000
Calibration Level [dBm]	-7.45	Freg Step Sweep[%]	1
		Dwell Time Sweep[s]	1
		Constant Frequency[Hz]	150000
		Mode	sweep
Calibrate	Abort Calibration Save Calibration File		
Level 3 V	6 ♀ dB RF-in Tekbox CDN RF-in Tekbox CDN Bell 1000 ↓ dB 1000 ↓ dB Calibration Level(dBm)	Freq: Messages	Clear Save

screenshot of the CDN immunity test feature of EMCview Pro

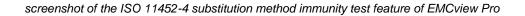
Immunity Test Setup C	alibration	Immunity Measurement EN 610	000-4-6 BCI
Parameter	Value	Parameter	Value
Freq Start[Hz]	150000	Calibration	none
Freq Stop[Hz]	8000000	Freg Start Sweep[Hz]	150000
Freq Step[%]	10	Freq Stop Sweep[Hz]	80000000
Calibration Level [dBm	ı] -17.91	Freq Step Sweep[%]	1
		Dwell Time Sweep[s]	1
		Constant Frequency[Hz]	150000
		Mode	sweep
Calibrate	Abort Calibration Save Calibration File	Current Probe	none
EN 61000-4-6 CDN 1	Required RF power[dBm][W] 35.09 dBm = 3.23 W Tekbox Modulated Amplifier Spectrum Analyzer	Freq: Messages TG:	Current monitoring

screenshot of the EN 61000-4-6 BCI immunity test feature of EMCview Pro





Immunity Test Setup Cali	bration	-Immunity Measur	ement ISO 11	452-4 SM	
Parameter	Value	Parameter		Value	
Freq Start[Hz]	1000000	Calibration		none	[]
Freq Stop[Hz]	40000000	Freq Start Swe	eep[Hz]	1000000	_
Freq Step[%]	10	Freq Stop Swe	eep[Hz]	40000000	
Calibration Level [dBm]	-7.45	Freq Step Swe	ep[%]	1	
VSWR Bridge	none	Dwell Time Sv	weep[s]	1	
		Constant Freq	uency[Hz]	1000000	
Calibrate	Abort Calibration Save Calibration File	Mode		sweep	
Level T	stor I 61000-4-6 BCI ISO 11452-4 SM ISO 11452-4 CL Substitution method, calibration, step 1 Tekbox Modulated Amplifier AM Spectrum Analyzer	Messages			turing pause
	RMS (dBm) Peak (dBm) -7.45	TG:			¥



	Immunity Measurement ISO 1	1452-4 CL	
	Parameter	Value	
	Freq Start Sweep[Hz]	1000000	
	Freq Stop Sweep[Hz]	400000000	
	Freq Step Sweep[%]	1	
	Dwell Time Sweep[s]	1	
	Constant Frequency[Hz]	1000000	
	Mode	sweep	
	Level [mA]	60	
	Current Probe	none	
EN 61000-4-6 CDN EN 61000-4-6 BCI ISO 11452-4 SM ISO 11452-4 CL Closed Loop Method Level The Modulated Amplifier BCI RF Current Modulated Amplifier AM Spectrum Analy Probe Rt Current Monitoring Probe Rt Current Monitoring Probe Rt Current Monitoring RMS [mA] Peak 1 60 60 60	8 ⁵ N		Clear Save Chart

screenshot of the ISO 11452-4 closed loop immunity test feature of EMCview Pro



WARNING:

Never connect the output of the TBMDA-CDN25 directly to the input of a spectrum analyzer. Check the maximum input ratings of the spectrum analyzer and protect it with an appropriate attenuator.

Open or shorted load is not recommended, potentially can cause damage of the RF output stage. Use $a \ge 3$ dB attenuator at the amplifier output, when driving loads with poor SWR.

Example: Rigol DSA815 – maximum input power rating: +20dBm

7 Ordering Information

Part Number	Description	
TBMDA-CDN25-EU	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 6 dB attenuator, 1 pc 30dB / 50W attenuator with N-connectors, C13 Schuko power cord	
TBMDA-CDN25-US	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 6 dB attenuator, 1 pc 30dB / 50W attenuator with N-connectors, C13 US power cord	
TBMDA-CDN25-UK	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 6 dB attenuator, 1 pc 30dB / 50W attenuator with N-connectors, C13 English power cord	
TBMDA-CDN25-AU	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 6 dB attenuator, 1 pc 30dB / 50W attenuator with N-connectors, C13 Australian power cord	

Table 5 – Ordering Information

8 History

Version	Date	Author	Changes
V1.0	13.12.2022	Mayerhofer	Creation of the document
V1.1	25.12.2023	Mayerhofer	Update of Chapters 4, 5, 6

Table 6 – History

www.tekbox.com

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